

Monocrystalline Silicon Active matrix Reflective Light valve

<http://come.to/mosarel>

Herbert De Smet, Jean Van den Steen, Dieter Cuypers, Nadine
Carchon and André Van Calster,

Imec vzw & Ghent University

Ghent, Belgium



Cupid Microdisplays 2001



Overview

- Introduction
- Technological issues
- Project planning
- Problems test vehicle
- Problems demonstrator
- Successes
- Open issues
- Results
- The future
- Acknowledgements



Cupid Microdisplays 2001



Introduction

- Idea:
 - Show feasibility of ultra-high resolution Displays in LCOS technology
 - ASIC approach using existing foundry and LCD assembly house



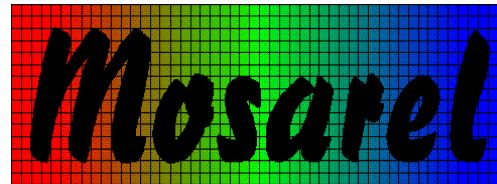
Cupid Microdisplays 2001



Introduction

- Project data :

- Esprit project EP25340
- Start date: 1/9/1997
- Initial duration: 24 months



- Consortium :

- | | |
|---------------------------------------|-------------------------|
| – Alcatel Microelectronics | Si Foundry (Asic house) |
| – Barco (co-ordinator) | End user |
| – Imec | Design & back-end tech. |
| – Thales Avionics (Sextant Avionique) | End user |
| – Thales Avionics LCD (Thomson LCD) | LCD assembly house |
| – University of Stuttgart | Study of LC effects |



Technological issues

- Chip size
 - active matrix area: 38x31 mm
 - bigger than field size of stepper (20x20 mm)
- Planarization, light shield, reflectivity
- Pixel clock
 - 80 Hz frame rate : 420 MHz pixel clock needed
- Voltage requirements
 - LC: 4-5 Vrms = 8-10 Vpp
 - C07 technology: max. 5 V

Stitching

Back-end

Parallelism

SDEMOS

Technological issues (2)

- Reflective LC effects
 - PDLC, HAN-cell, SCTN, 52-54° RTN,
Fréedericksz, DAP (VAN)
- Spacer visibility
 - spacer size \leq pixel size
 - (except VAN)

Stuttgart

Spacerless



Cupid Microdisplays 2001



Stitching

- Active Matrix = 38.4x30.7 mm²
- Stepper lithography: max field size = 20x20 mm² = max die size.
- Stitching:

- split up design in smaller modules that fit on one mask reticle

TL	T	TR
L	C	R
BL	B	BR

Reticle

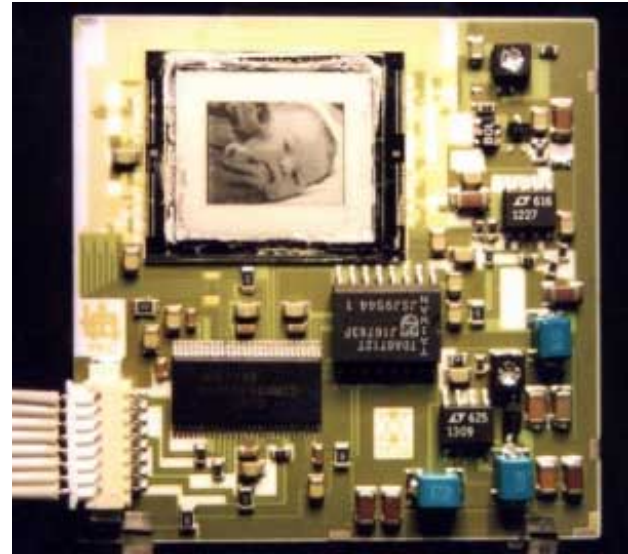


TL	T	T	T	T	T	TR
L	C	C	C	C	C	R
L	C	C	C	C	C	R
L	C	C	C	C	C	R
BL	B	B	B	B	B	BR

Die

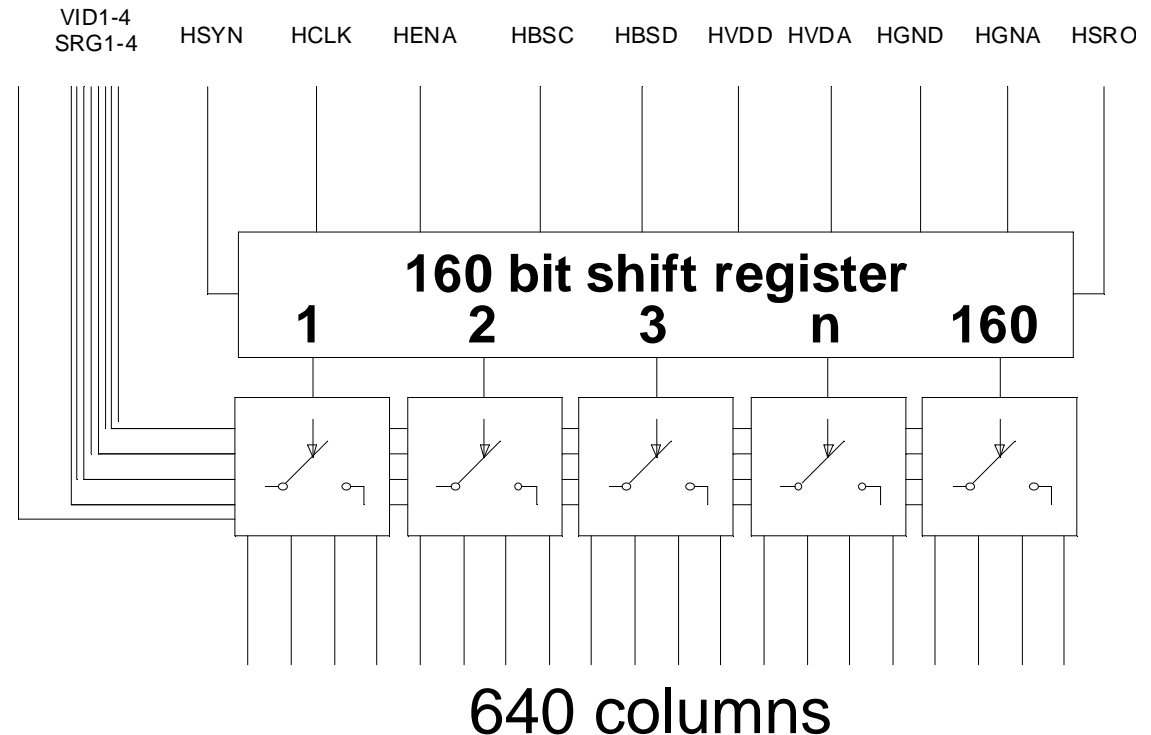
Modified back-end process

- Planarization:
 - organic materials (OLIN)
 - SOG (spin-on glass)
 - CMP (expensive)
- Light shield:
 - Black polyimide (Brewer science DARC)
 - TiN (AR coating)
- Pixel reflectivity
 - unsintered aluminium, cold sputtering



Parallelism in drivers

- GXGA, 80 Hz -> pixel clock = 420 MHz >> .7 μ m CMOS
- Parallelism
- 4 x 4 = 16

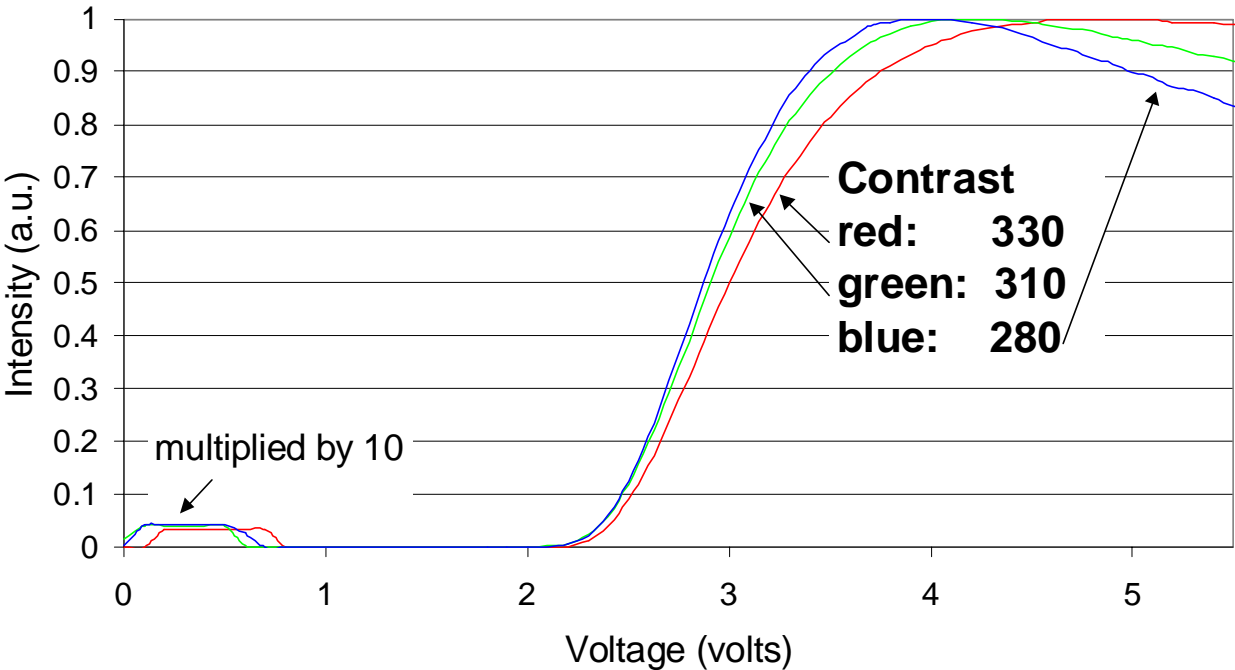


SDEMOS

- Reflective LC effects : 4-5 V_{RMS}
- Projector with continuous light source:
 - DRAM type active matrix: no backplane switching
 - $2xV_{\text{RMS}}$ to be switched by pixels transistors
 - V_{Gate} : 10-14 V (incl. body effect)
- Mosarel: C07 : max. 5 volts
⇒ Symmetrical Drain Extended MOS (SDEMOS):
up to 15 V

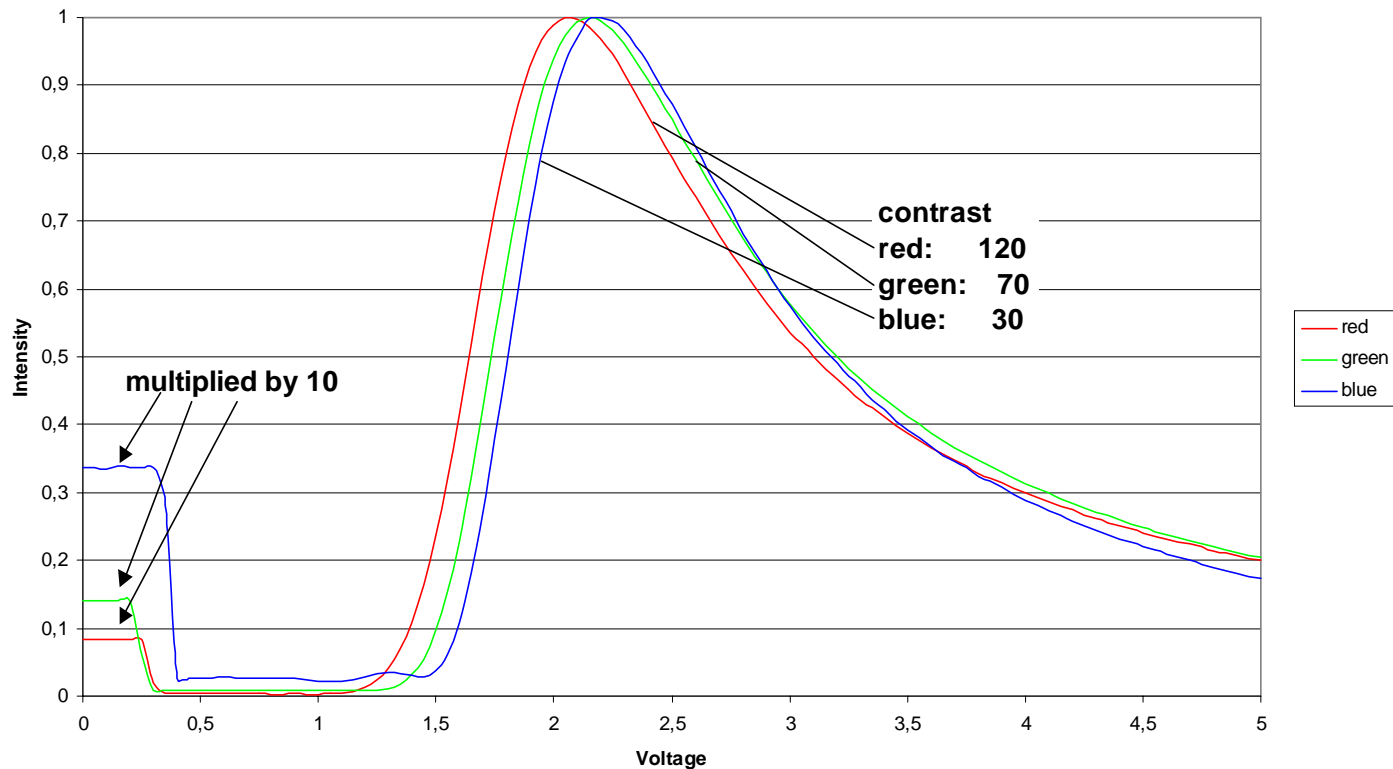
LC effects

Vertically Aligned Nematic Cell



LC effects (2)

52° TN cell gap: 5.0μm

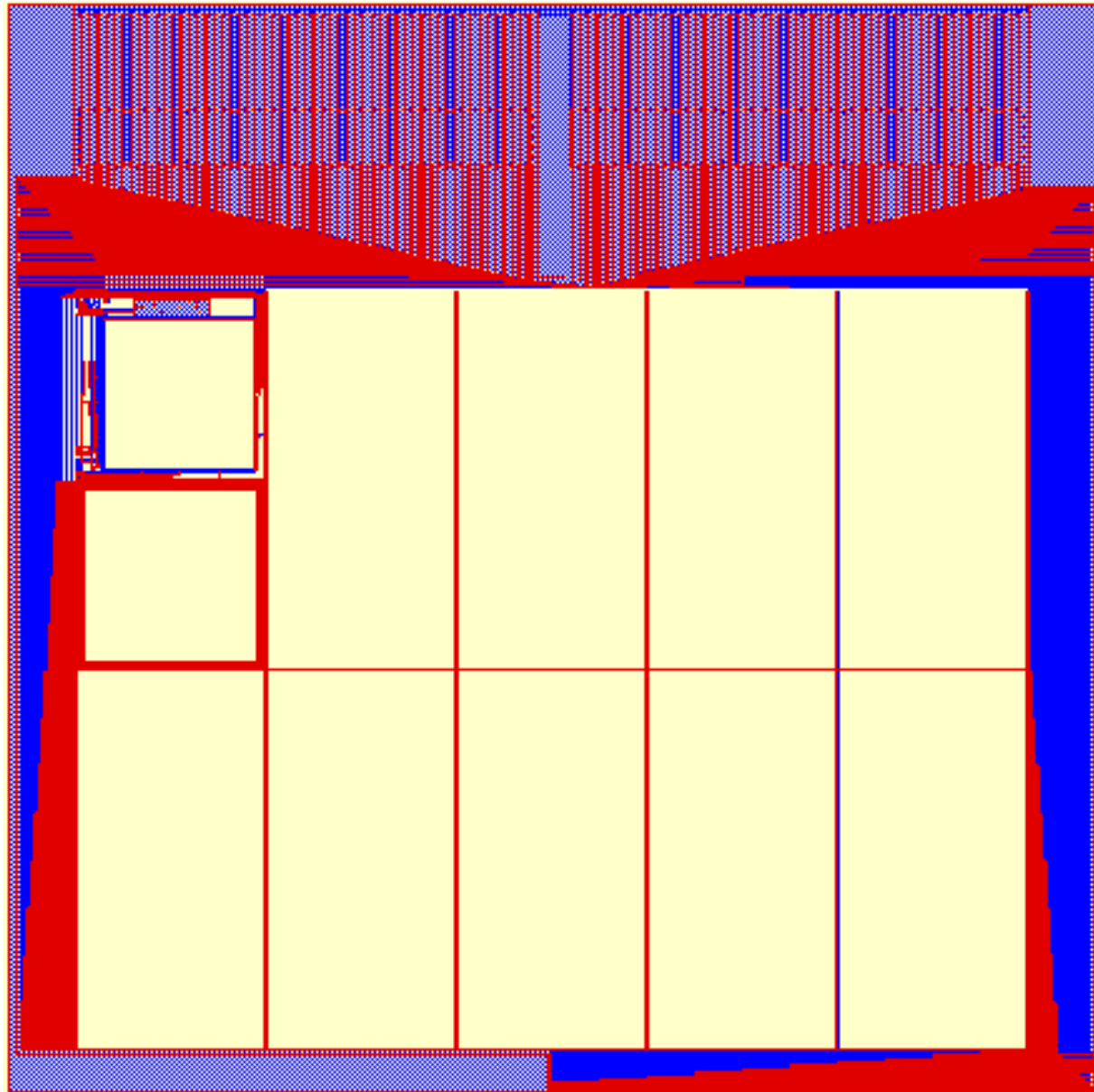


Project planning

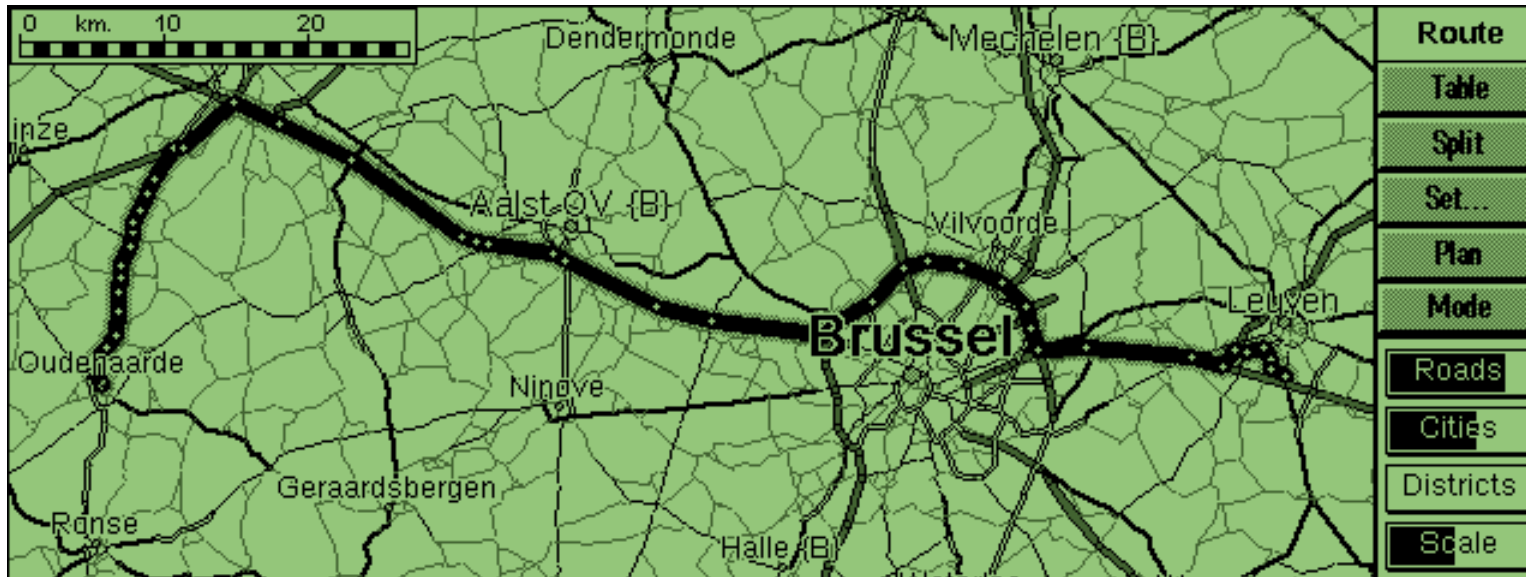
- 2 phases :
 - Test vehicle (15 months)
 - full resolution (2560x2048 pixels)
 - no integrated drivers (addressing in row and column blocks)
 - testing DEMOS pixel transistors
 - testing the back-end technology and stitching
 - testing spacerless assembly
 - electro-optical performance evaluation
 - Final demonstrator (9 months)
 - integrated row and column drivers, with parallelism and redundancy
 - workstation and HUD demonstrator
 - **high-speed peripheral electronics**
 - **optical systems**

Problems test vehicle

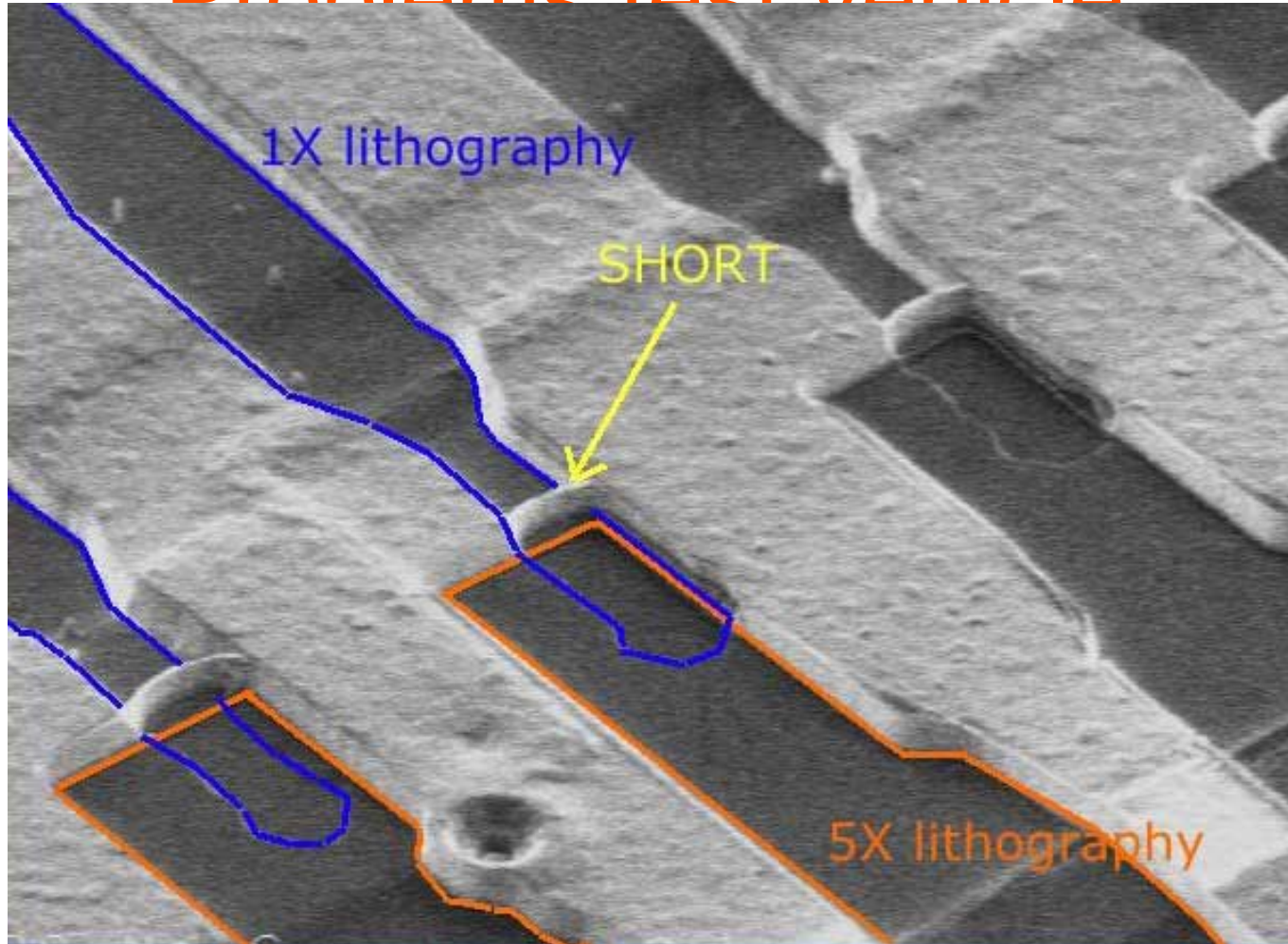
- Organic materials incompatible with stepper lithography (5X)
 - back-end process in 1X litho
- Test vehicle w/o integrated drivers (block addressing):
 - routing around matrix not repetitive - not stitchable
 - routing in 1X, matrix in 5X (back-end in 1X tech.)
- Design: mix & match 1X & 5X lithography + stitching = trouble
- Processing: mix & match in 2 different clean rooms (Leuven - Oudenaarde)
- Shorts (1): (massive short all rows & columns)
 - due to conductive stringers between 1X and 5X
- Shorts (2): (many shorted blocks)
 - due to 1X litho in matrix region + block structure of T.V.



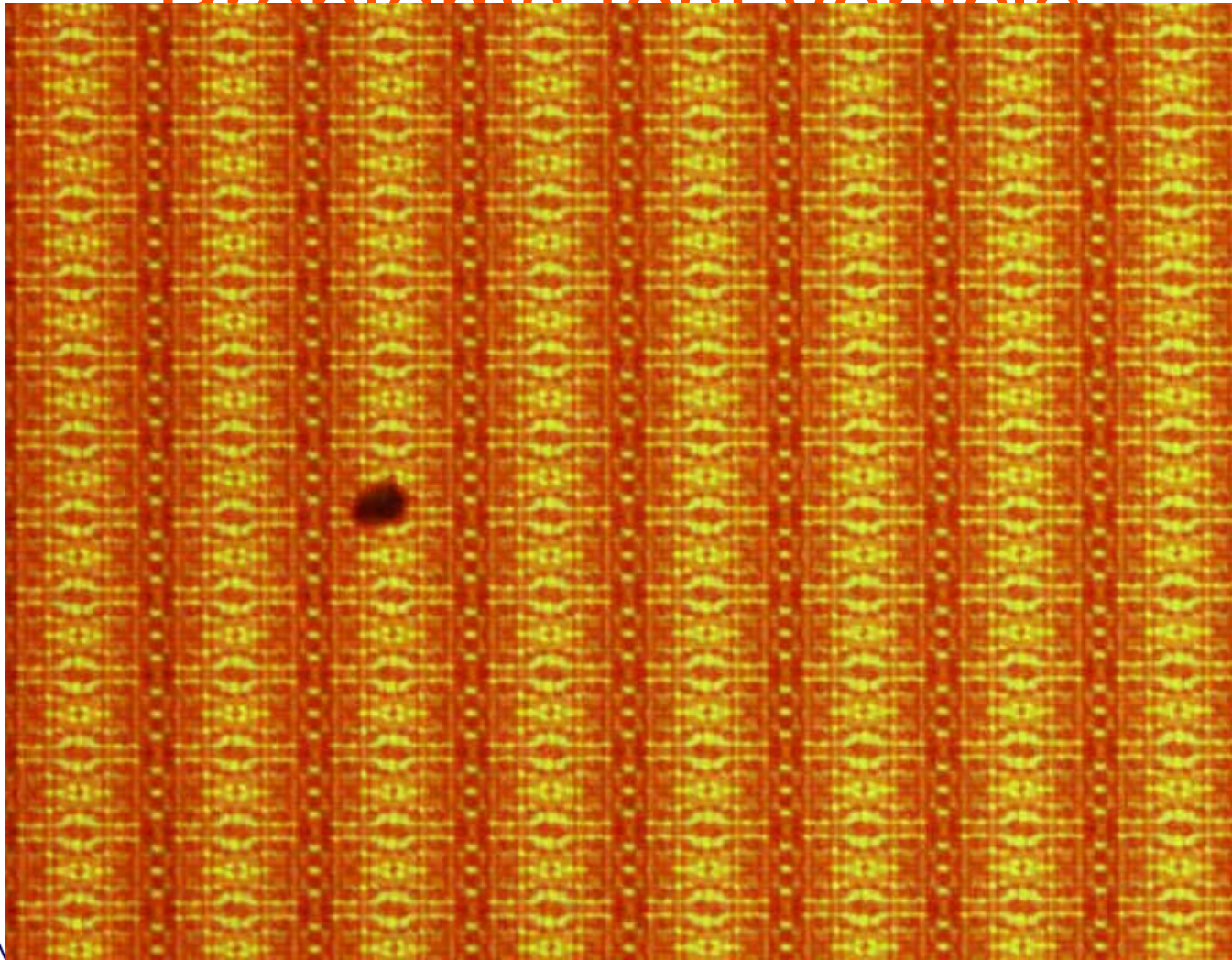
Problems test vehicle



Problems test vehicle



Problems test vehicle



Problems test vehicle (2)

- several months delay accumulated

Change of plan:

- Abandon organic material based back-end process
 - TiN light shield and CMP planarization
- Final demonstrator completely in 5X stepper lithography (no mix & match)

Problems demonstrator

- Automatic design rule checking not compatible with stitching
 - Manual checking necessary
- Redundancy features of drivers contain error:
 - Drivers work but reduced redundancy
- Shorts (3)
 - due to CMP step
 - would require redesign and more CMP steps (like C035 process)



Cupid Microdisplays 2001



Successes

- Stitching
- DEMOS
- pixel aperture ratio
- pixel planarity
- AI reflectivity
- light shield
- driver design (except redundancy)
- spacerless assembly in test vehicle

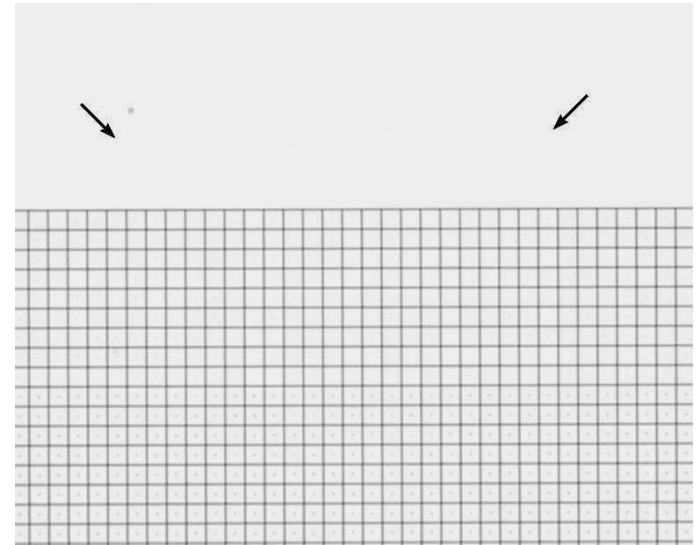


Cupid Microdisplays 2001



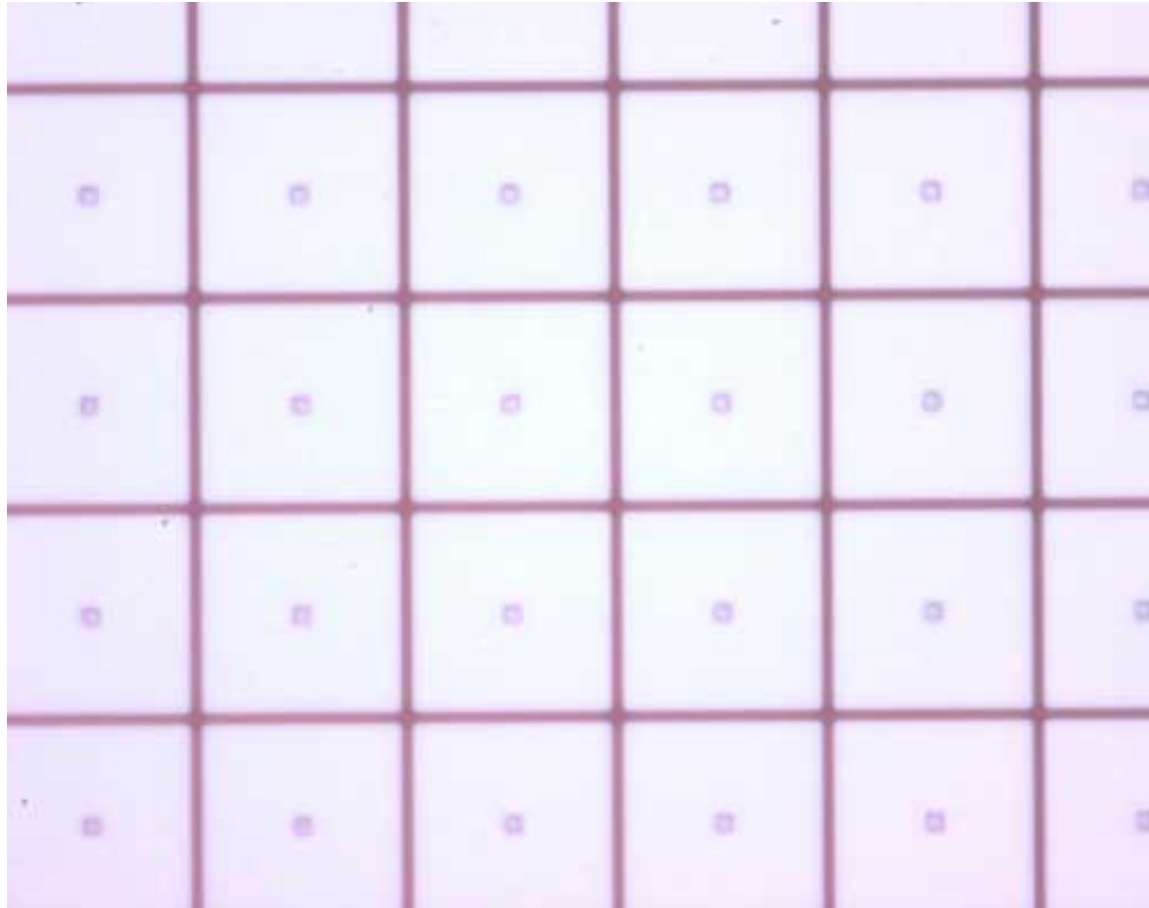
Stitching

- Technical result very good:
 - < 50 nm positioning error
 - stitching lines nearly invisible



- makes different display formats possible with one mask set: GXGA, SXGA, XGA-p

Pixel aperture ratio

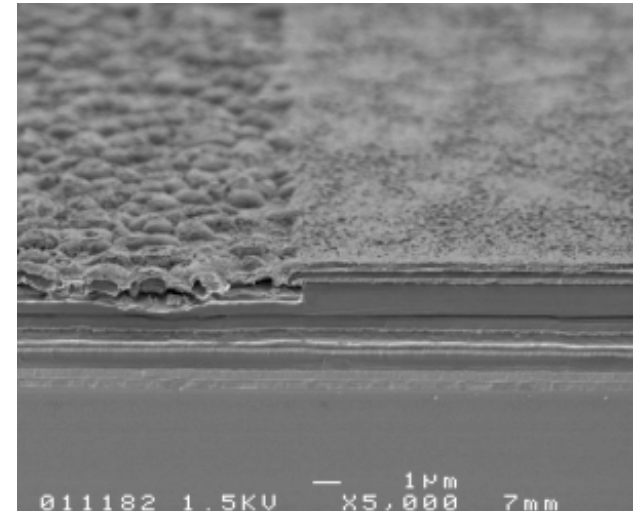
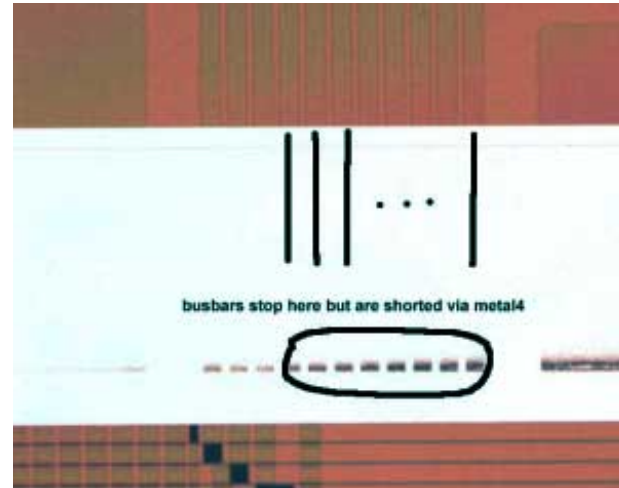


Open issues

- CMP shorts
- planarity outside matrix
- spacerless assembly of demonstrator
- redundancy in driver circuit
- yield (?)

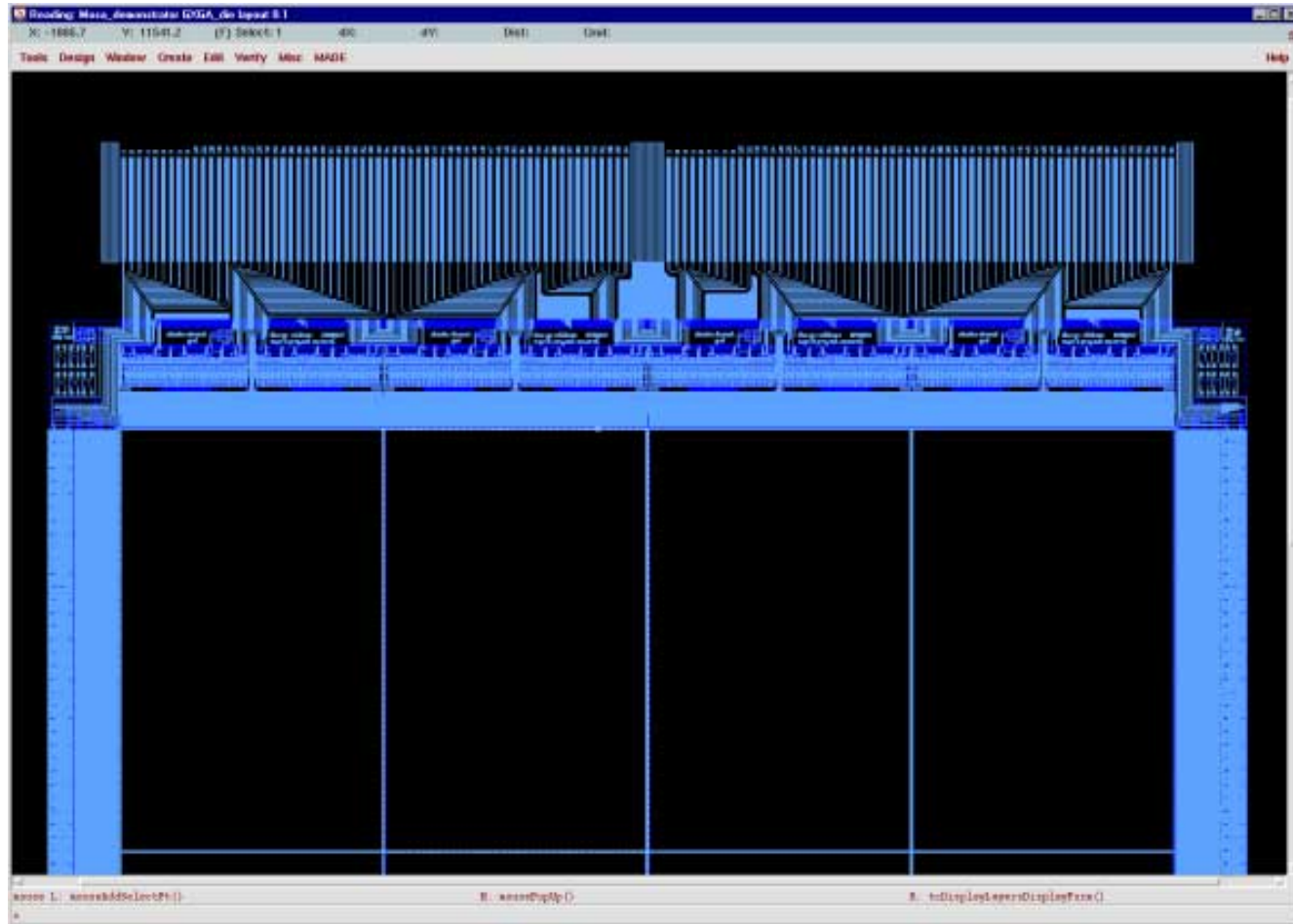
CMP

- Shorts



- Chip topology must be limited
 - Dummy metal algorithms:
 - Difficult to combine with stitching
 - More difficult for larger chips

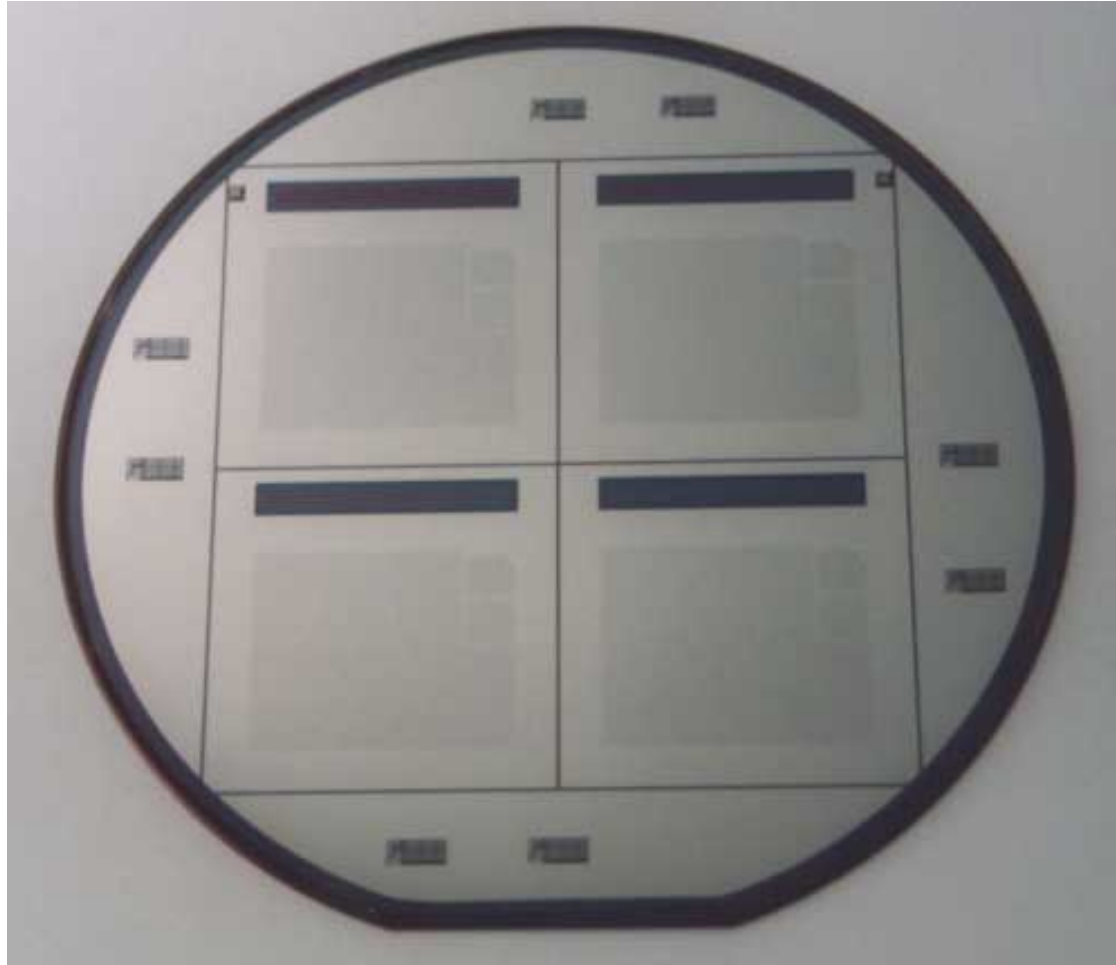
Results



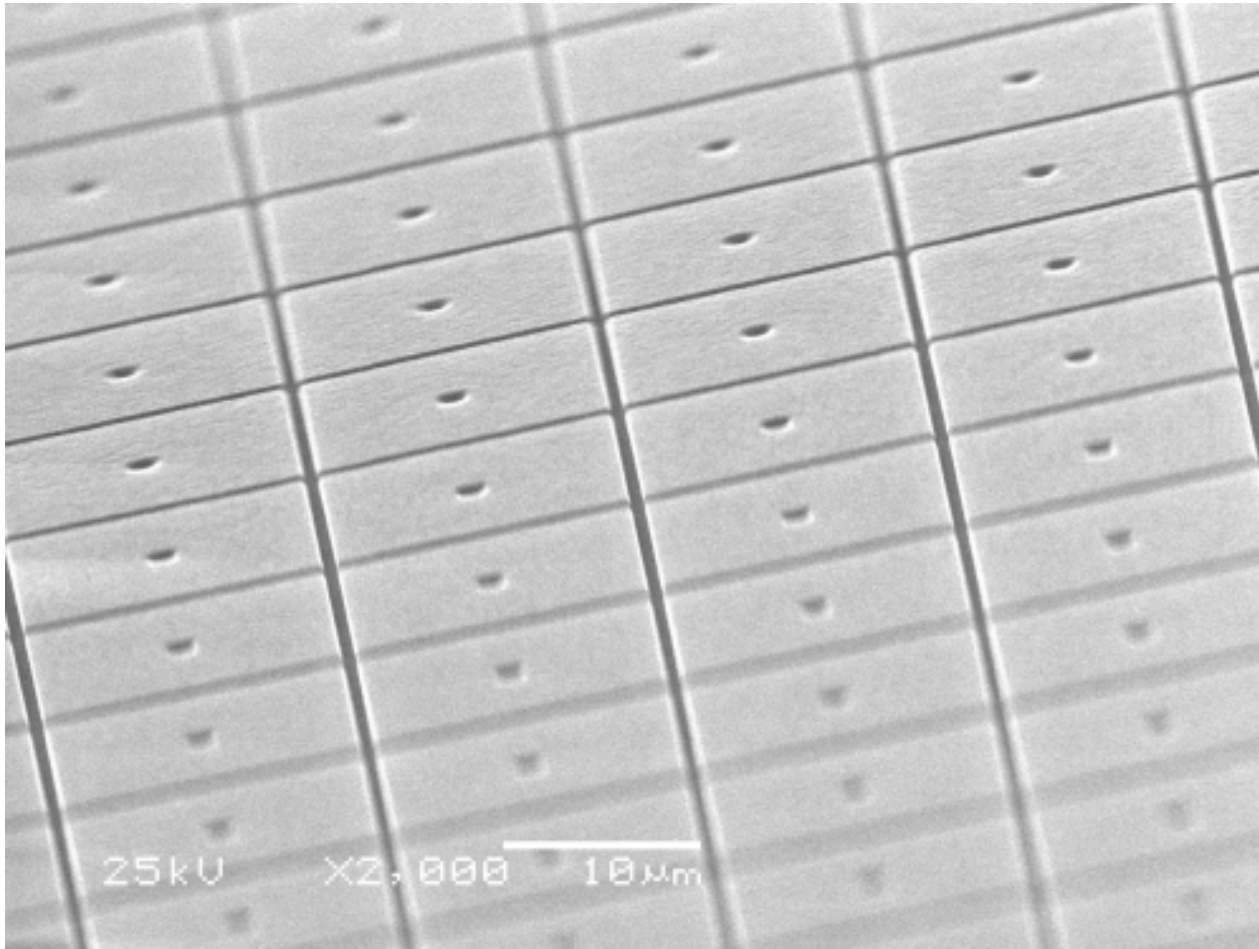
Cupid Microdisplays 2001



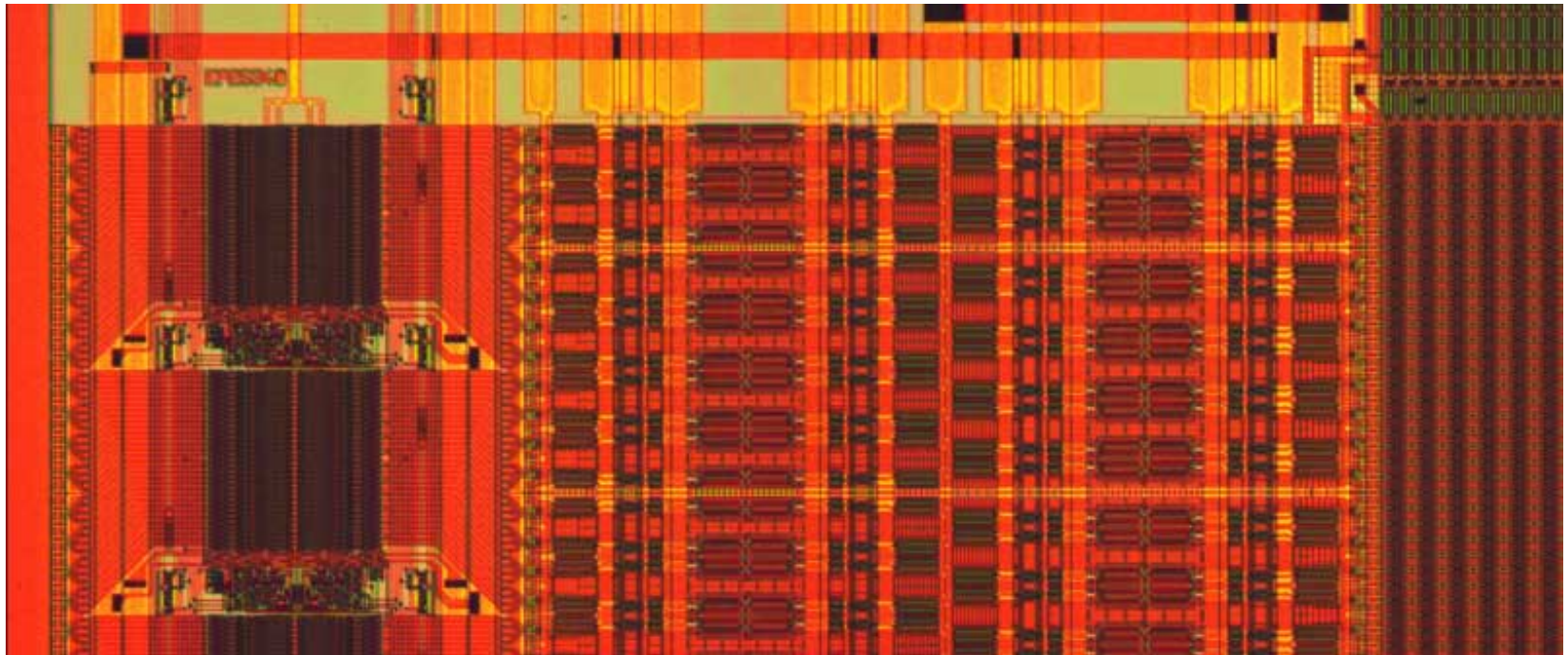
Results



Results



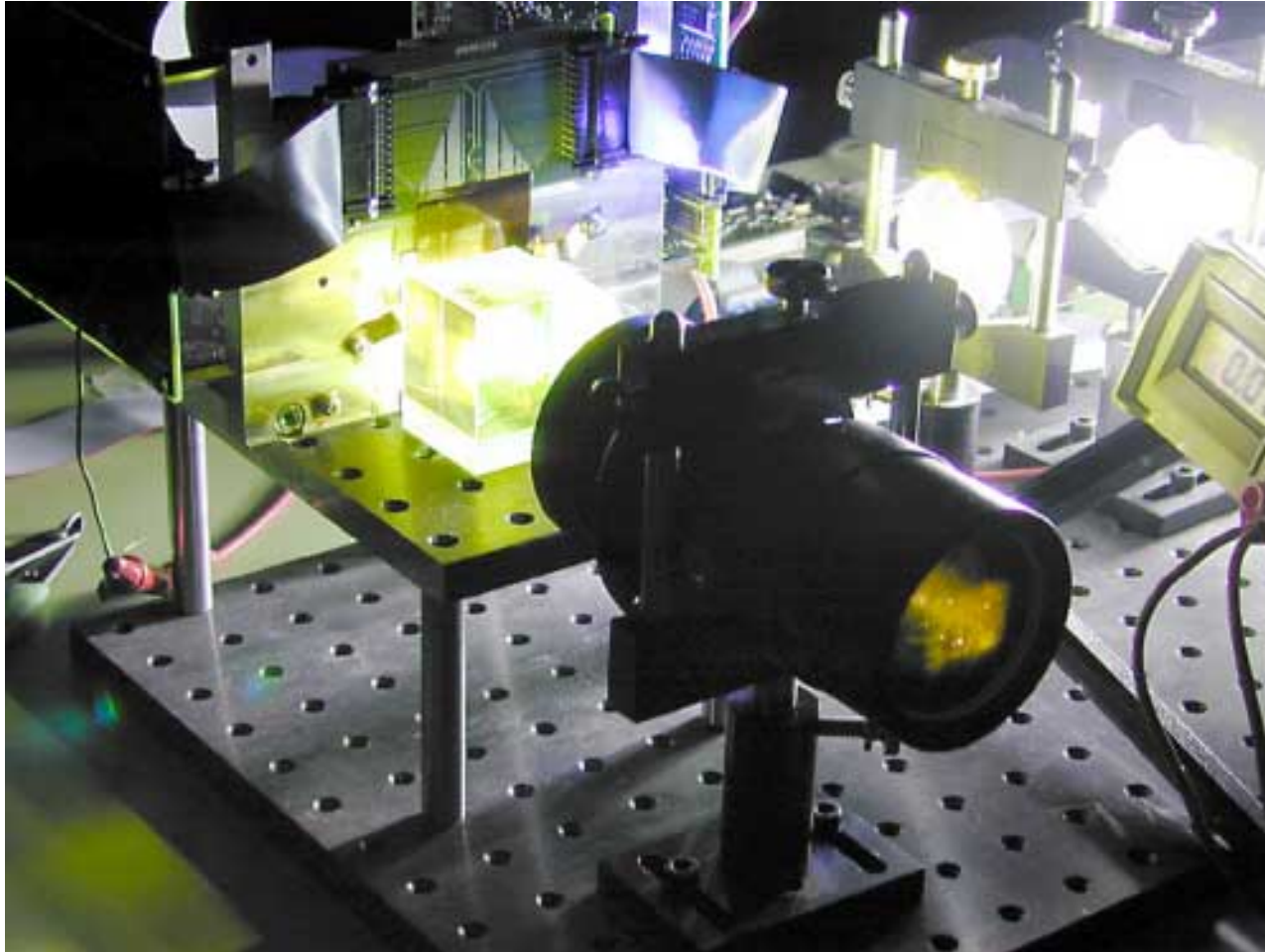
Results



Results



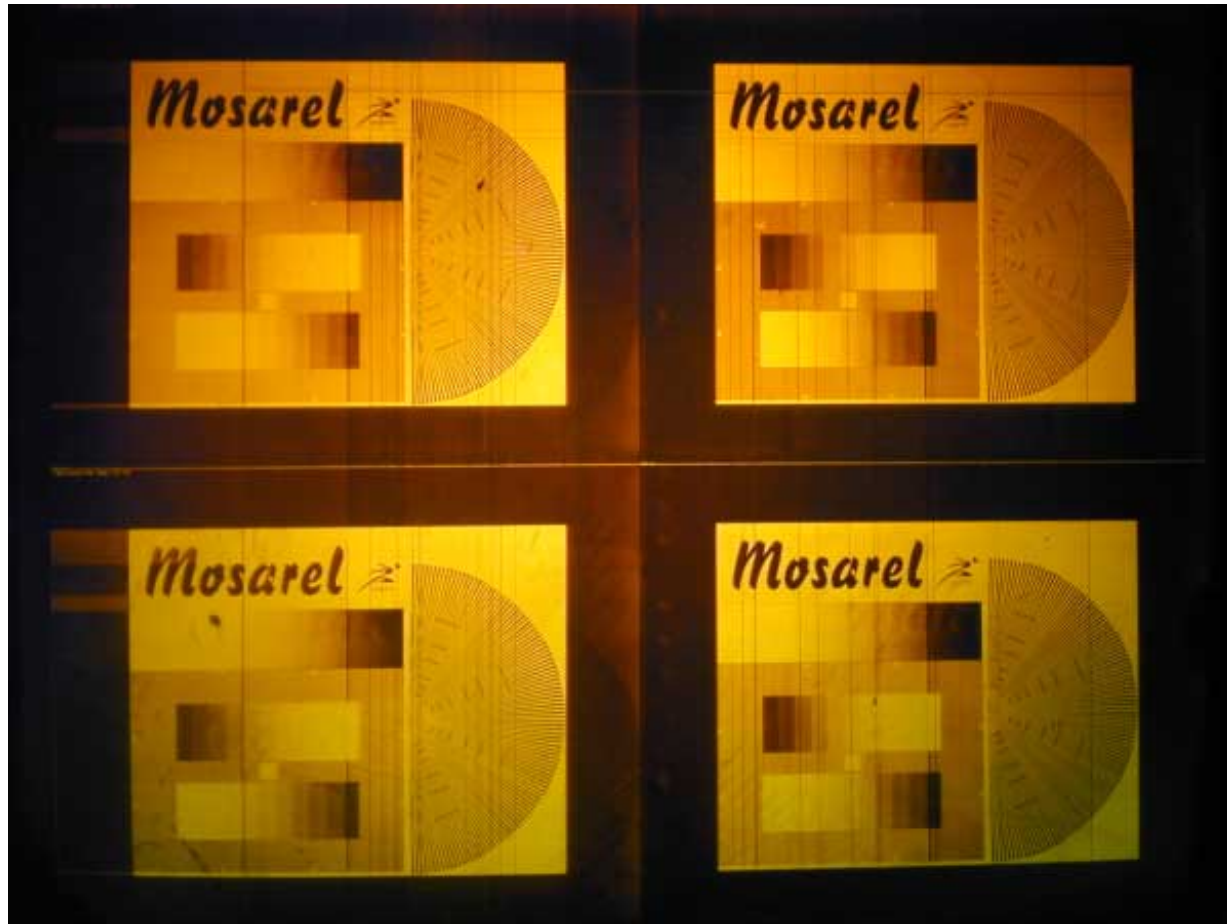
Results



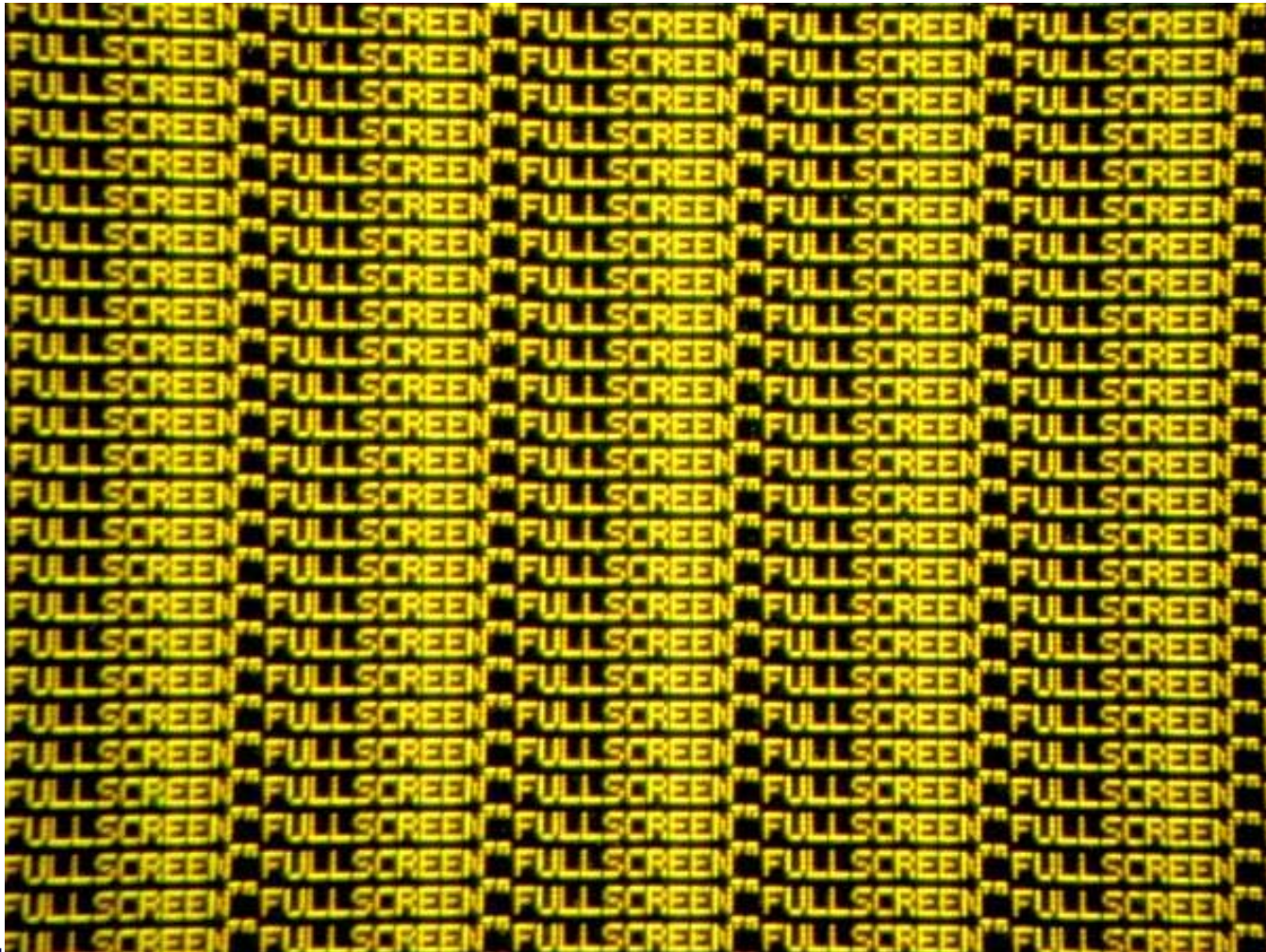
Results



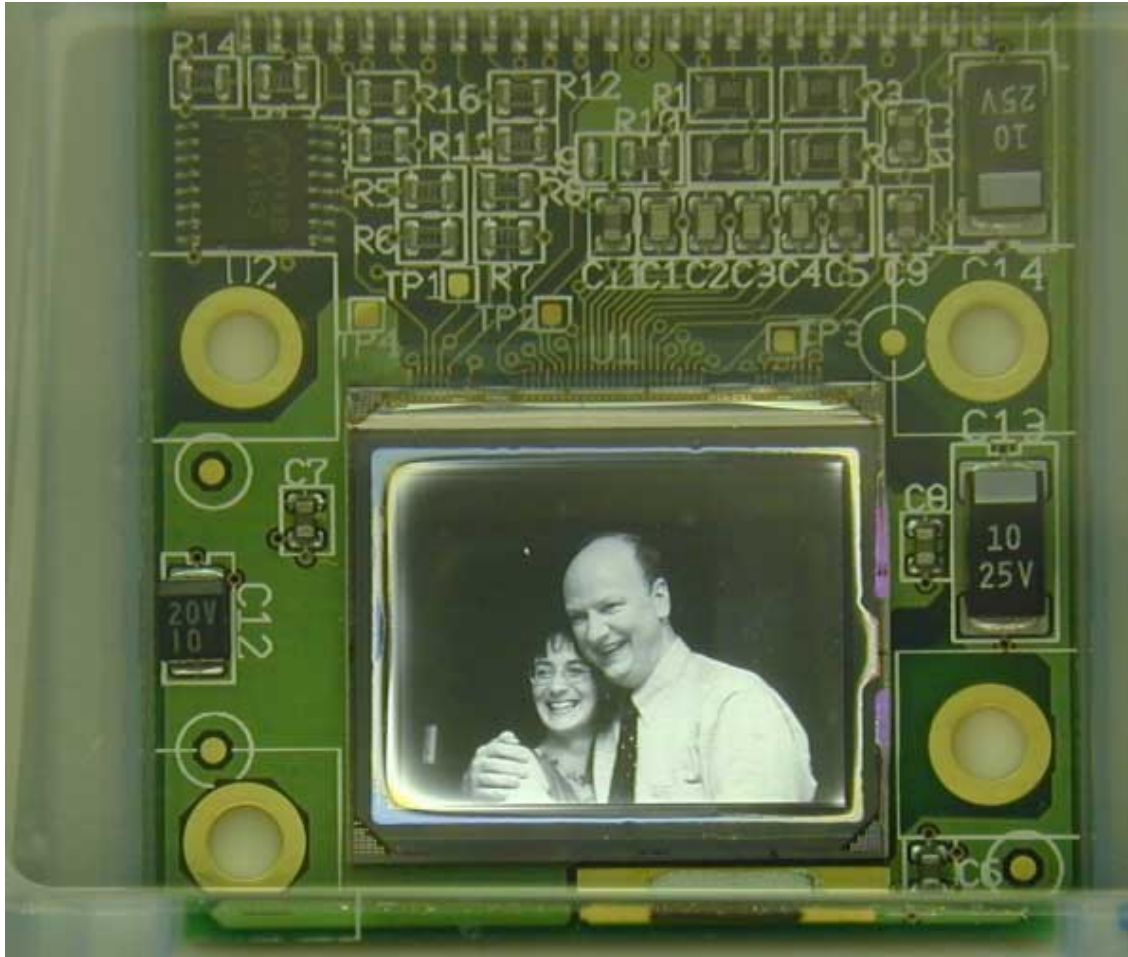
Results



Results



The future



Acknowledgements

The authors wish to thank:

- EU 4th framework ESPRIT program
 - Alcatel Microelectronics, Barco, Thales Avionics, Thales LCD, University of Stuttgart
-



Cupid Microdisplays 2001

